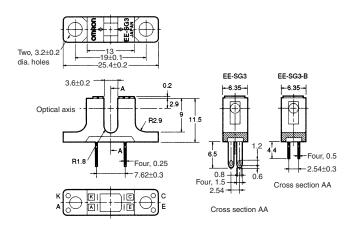
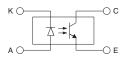
Photomicrosensor (Transmissive)

■ Dimensions

Note: All units are in millimeters unless otherwise indicated.



Internal Circuit



Terminal No.	Name
Α	Anode
K	Cathode
С	Collector
E	Emitter

Unless otherwise specified, the tolerances are as shown below.

Dimensions	Tolerance
3 mm max.	±0.3
3 < mm ≤ 6	±0.375
6 < mm ≤ 10	±0.45
10 < mm ≤ 18	±0.55
18 < mm ≤ 30	±0.65

■ Features

- · Dust-proof model.
- Solder terminal model (EE-SG3).
- PCB terminal model (EE-SG3-B).
- RoHS Compliant.

■ Absolute Maximum Ratings (Ta = 25°C)

	Item	Symbol	Rated value
Emitter	Forward current	I _F	50 mA (see note 1)
	Pulse forward current	I _{FP}	1 A (see note 2)
	Reverse voltage	V_R	4 V
Detector	Collector-Emitter voltage	V_{CEO}	30 V
	Emitter-Collector voltage	V _{ECO}	
	Collector current	I _C	20 mA
	Collector dissipation	P_{C}	100 mW (see note 1)
Ambient temperature	Operating	T _{opr}	–25°C to 85°C
	Storage	T _{stg}	-30°C to 100°C
Soldering temperature		T _{sol}	260°C (see note 3)

- Note: 1. Refer to the temperature rating chart if the ambient temperature exceeds 25°C.
 - 2. The pulse width is 10 μs maximum with a frequency of 100 Hz.
 - 3. Complete soldering within 10 seconds.

■ Ordering Information

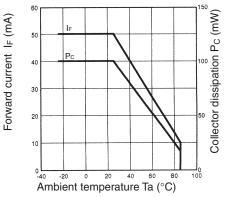
Description		Model
Photomicrosensor (transmissive)	Solder terminal	EE-SG3
	PCB terminal	EE-SG3-B

■ Electrical and Optical Characteristics (Ta = 25°C)

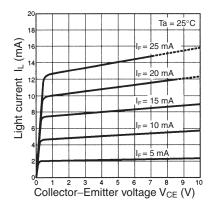
	Item	Symbol	Value	Condition
Emitter	Forward voltage	V _F	1.2 V typ., 1.5 V max.	I _F = 30 mA
	Reverse current	I _R	0.01 μA typ., 10 μA max.	V _R = 4 V
	Peak emission wavelength	λ_{P}	940 nm typ.	I _F = 20 mA
Detector	Light current	I∟	2 mA min., 40 mA max.	I _F = 15 mA, V _{CE} = 10 V
	Dark current	I _D	2 nA typ., 200 nA max.	V _{CE} = 10 V, 0 ℓx
	Leakage current	I _{LEAK}		
	Collector–Emitter saturated voltage	V _{CE (sat)}	0.1 V typ., 0.4 V max.	I _F = 30 mA, I _L = 1 mA
	Peak spectral sensitivity wavelength	λ_{P}	850 nm typ.	V _{CE} = 10 V
Rising time		tr	4 μs typ.	$V_{CC} = 5 \text{ V}, R_L = 100 \Omega, I_L = 5 \text{ mA}$
Falling time		tf	4 μs typ.	$V_{CC} = 5 \text{ V}, R_L = 100 \Omega, I_L = 5 \text{ mA}$

■ Engineering Data

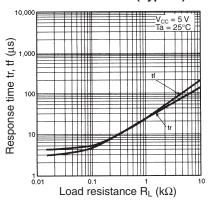
Forward Current vs. Collector **Dissipation Temperature Rating**



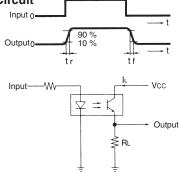
Light Current vs. Collector-Emitter **Voltage Characteristics (Typical)**



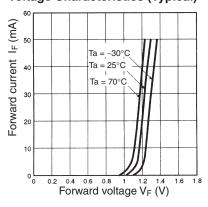
Response Time vs. Load Resistance Characteristics (Typical)



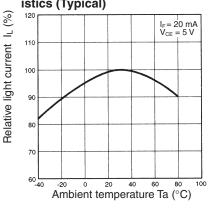
Response Time Measurement Circuit



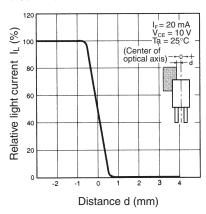
Forward Current vs. Forward Voltage Characteristics (Typical)



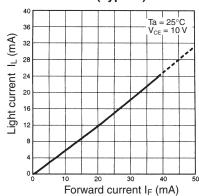
Relative Light Current vs. Ambient Temperature Characteristics (Typical)



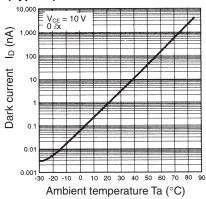
Sensing Position Characteristics (Typical)



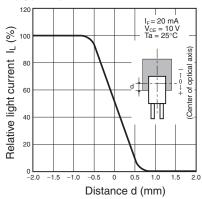
Light Current vs. Forward Current Characteristics (Typical)

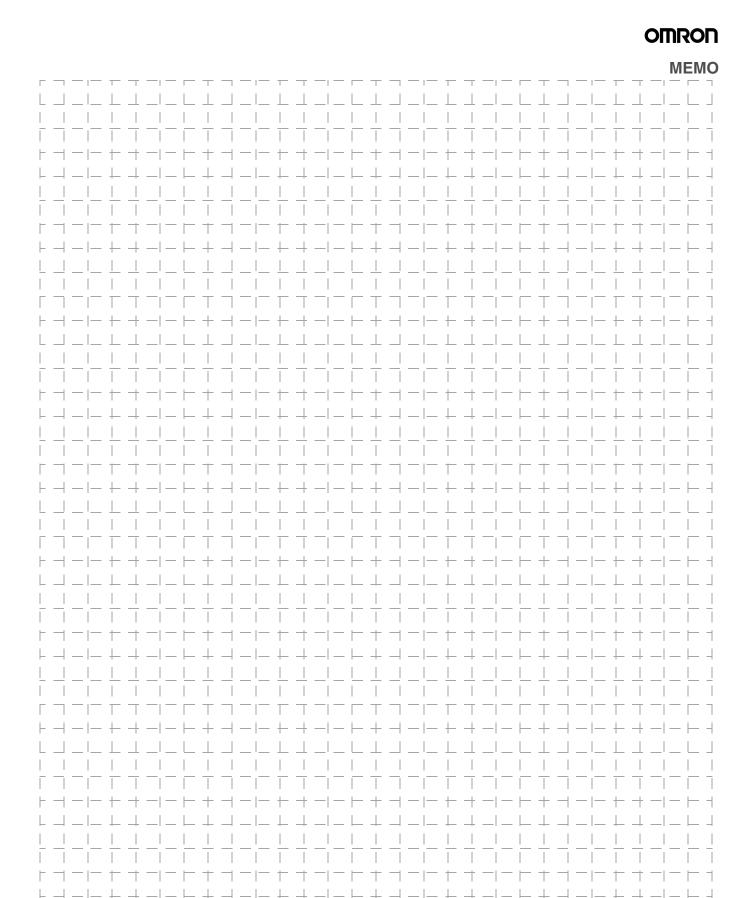


Dark Current vs. Ambient Temperature Characteristics (Typical)



Sensing Position Characteristics (Typical)







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ALL DIMENSIONS SHOWN ARE IN MILLIMETERS.

To convert millimeters into inches, multiply by 0.03937. To convert grams into ounces, multiply by 0.03527.

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Photomicrosensor (Transmissive) **EE-SG3/EE-SG3-B**